



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate DIODE

DK21LLD03 SWITCHING DIODE

DESCRIPTION

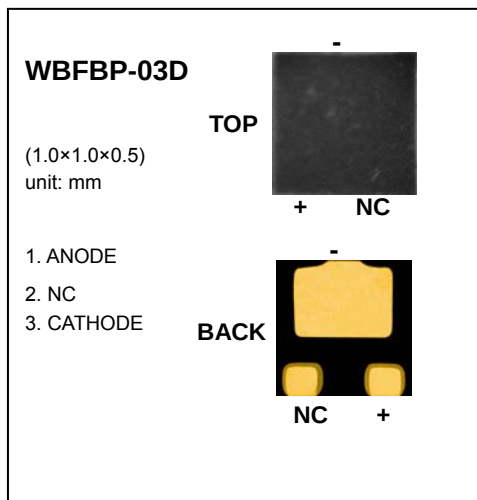
Epitaxial planar Silicon diode

FEATURES

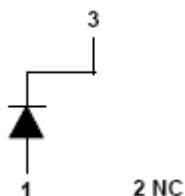
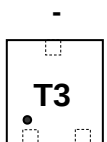
Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
DVD-ROM, Note book PC, etc.)



MARKING: T3



Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Forward Continuous Current	I _{FM}	400	mA
Average Rectified Output Current	I _O	200	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0μs @ t = 1.0s	I _{FSM}	2.5 0.5	A
Power Dissipation	P _D	100	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	1250	°C/W
Operating Junction Temperature	T _J	150	°C
Storage temperature	T _{STG}	-65-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	200		V
Reverse voltage leakage current	I_R	$V_R = 200V$		100	nA
Forward voltage	V_F	$I_F = 100mA$ $I_F = 200mA$		1 1.25	V
Total capacitance	C_T	$V_R = 0V, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 30mA, I_{rr} = 0.1XI_R,$ $R_L = 100\Omega$		50	nS

Typical Characteristics

DK21LLD03

